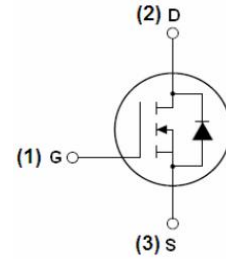




N-Channel Enhancement Mode Power MOSFET

Description

The MX6058 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.



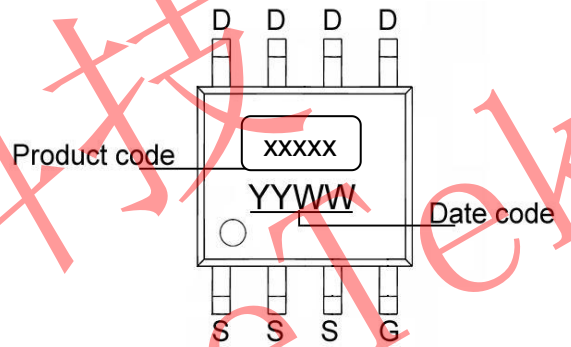
Schematic diagram

General Features

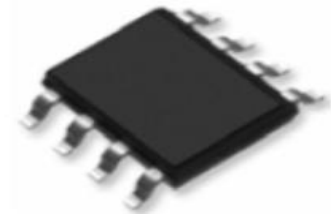
- ◆ $V_{DS} = 60V$, $I_D = 8A$
- ◆ $R_{DS(ON)}(Typ.) 13m\Omega @ V_{gs}=10V$
- ◆ High density cell design for ultra low Rds on
- ◆ Fully characterized Avalanche voltage and current

Application

Power switching application
Hard Switched and High Frequency Circuits
Uninterruptible Power Supply



Marking and pin assignment



SOP-8 top view

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	8	A
Drain Current-Continuous($T_C=100^\circ C$)	$I_D (100^\circ C)$	5.5	A
Pulsed Drain Current	I_{DM}	32	A
Maximum Power Dissipation	P_D	2.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$



Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.4	1.9	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =8A	-	13	16	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =7A	-	80	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, F=1.0MHz	-	2460	-	PF
Output Capacitance	C _{oss}		-	163	-	PF
Reverse Transfer Capacitance	C _{rss}		-	126	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, R _L =6.7Ω V _{GS} =10V, R _G =3Ω	-	7.4	-	nS
Turn-on Rise Time	t _r		-	5.1	-	nS
Turn-Off Delay Time	t _{d(off)}		-	28.2	-	nS
Turn-Off Fall Time	t _f	V _{DS} =20V, I _D =20A, V _{GS} =10V	-	5.5	-	nS
Total Gate Charge	Q _g		-	50	-	nC
Gate-Source Charge	Q _{gs}		-	6	-	nC
Gate-Drain Charge	Q _{gd}	-	15	-	nC	
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =20A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S	-	-	-	50	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =20A	-	28	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs ^(Note3)	-	40	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{θJA}	50	°C/W
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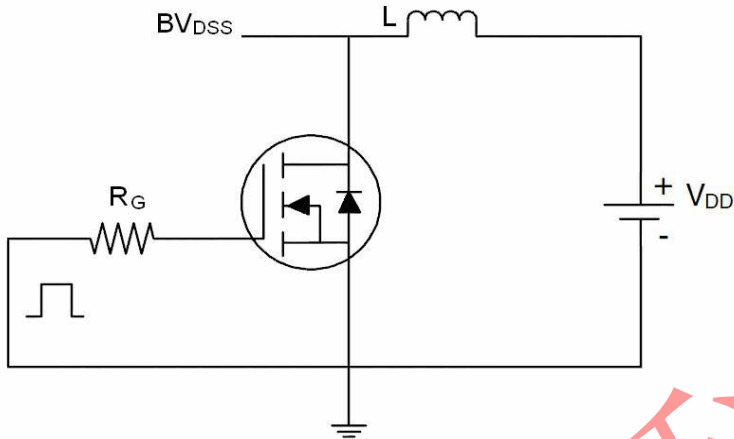
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

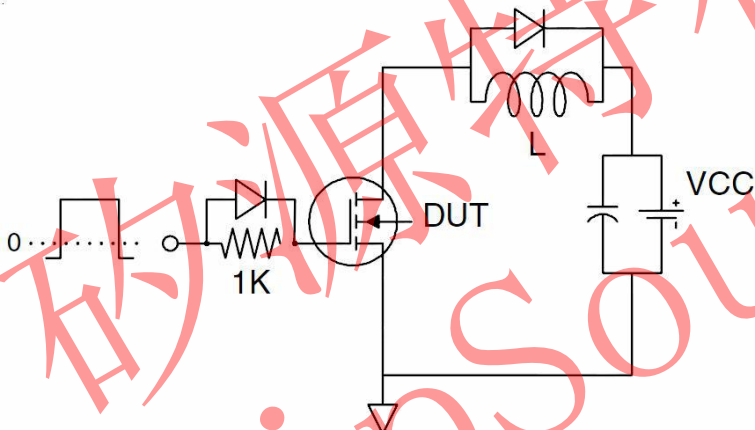


Test Circuit

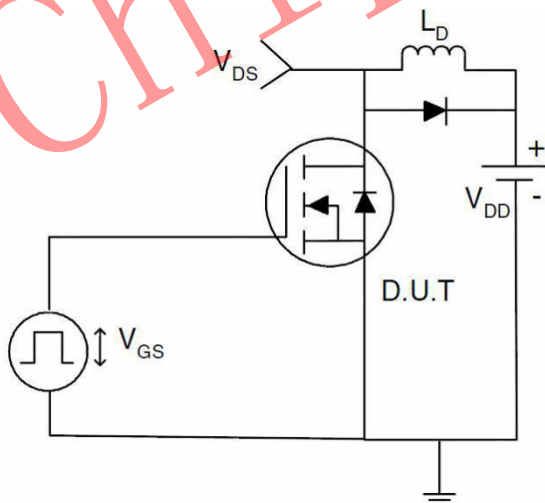
1) EAS Test Circuits



2) Gate Charge Test Circuit:



3) Switch Time Test Circuit:





Typical Electrical and Thermal Characteristics (Curves)

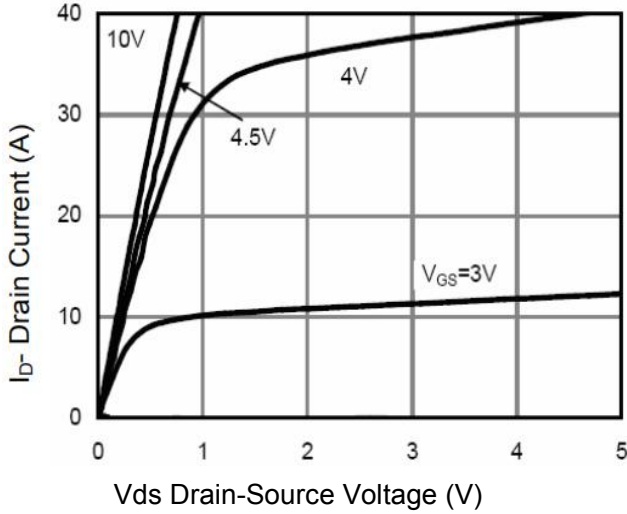


Figure 1 Output Characteristics

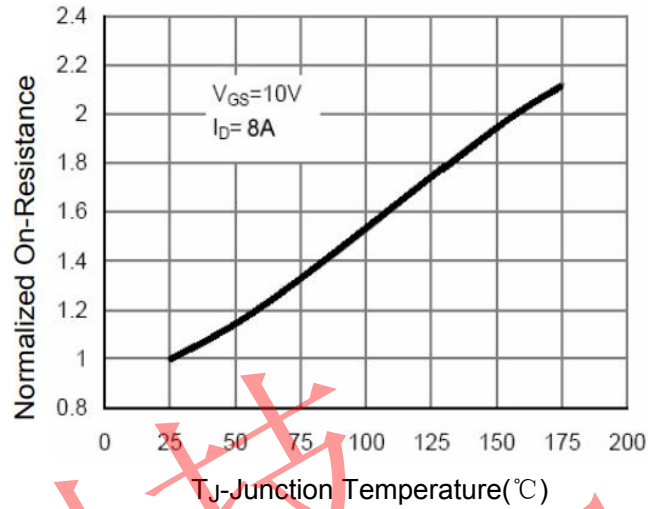


Figure 4 Rdson-Junction Temperature

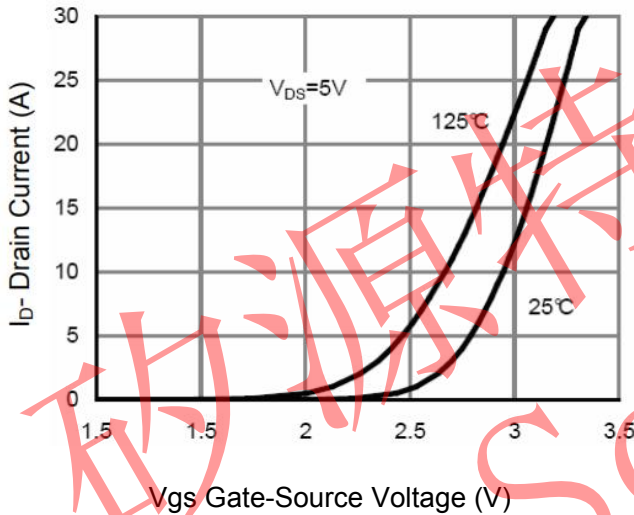


Figure 2 Transfer Characteristics

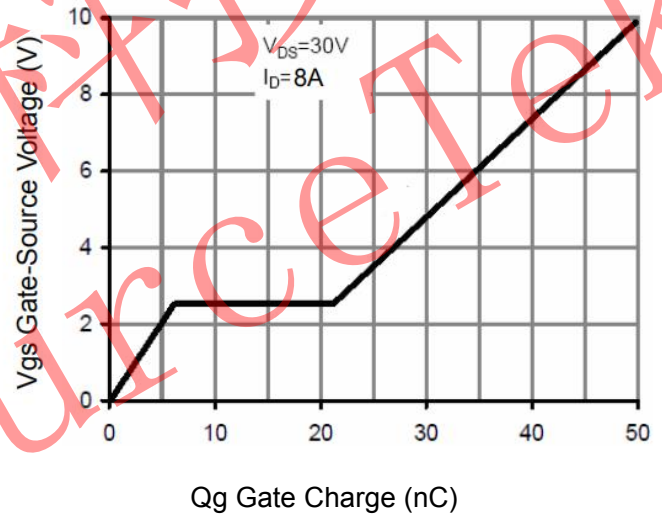


Figure 5 Gate Charge

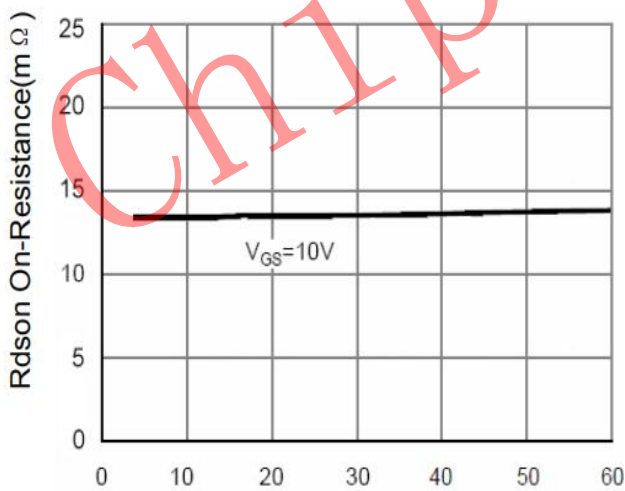


Figure 3 Rdson- Drain Current

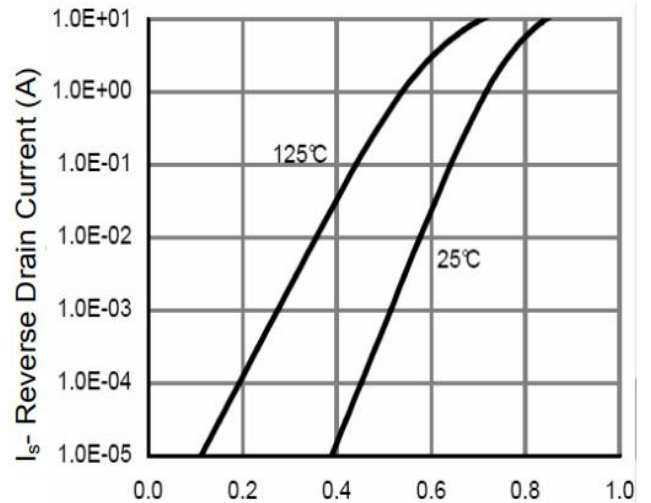


Figure 6 Source- Drain Diode Forward

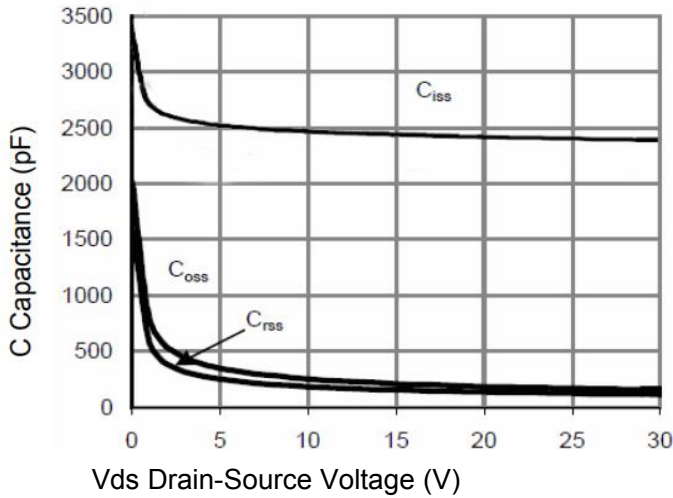


Figure 7 Capacitance vs Vds

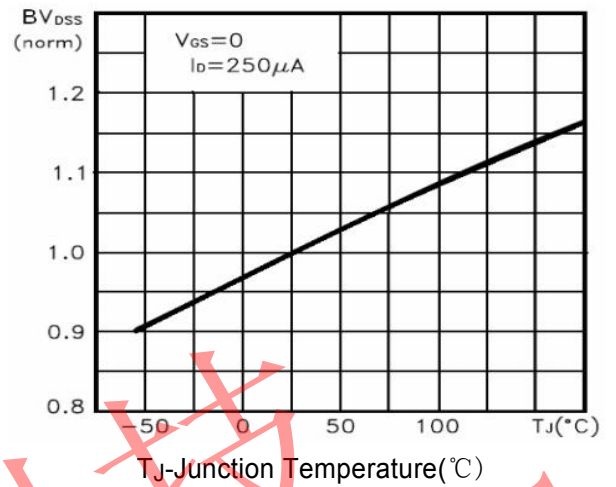


Figure 9 BVdss vs Junction Temperature

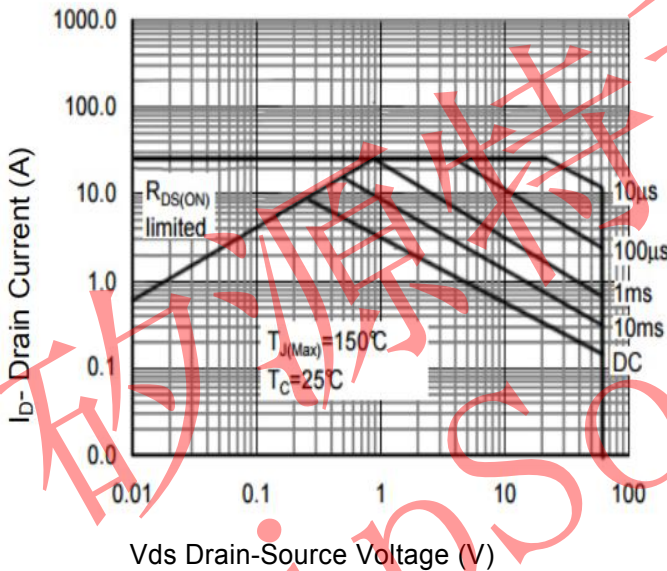


Figure 8 Safe Operation Area

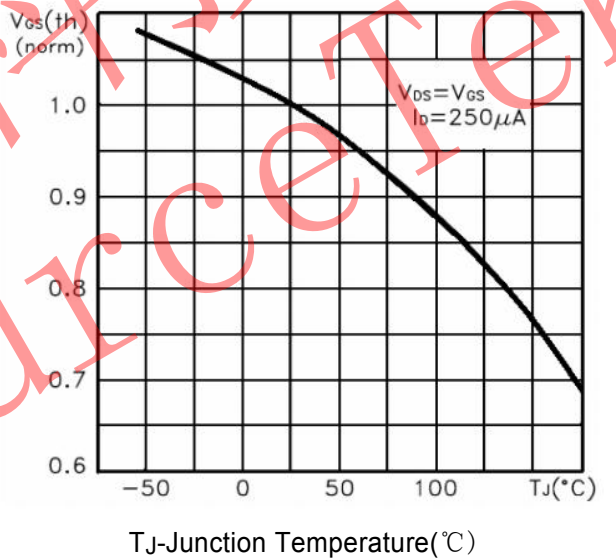


Figure 10 Vgs(th) vs Junction Temperature

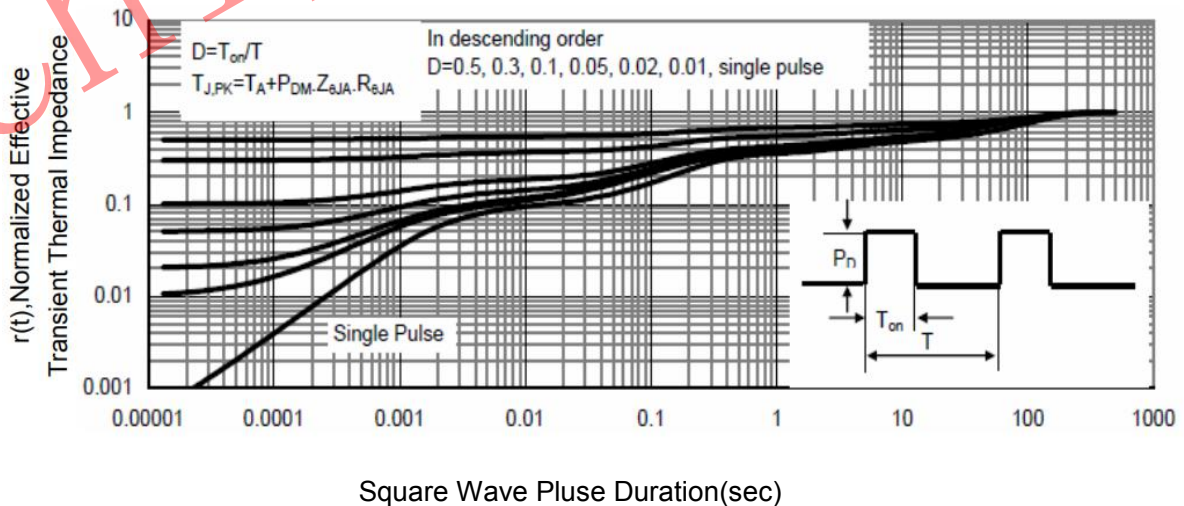
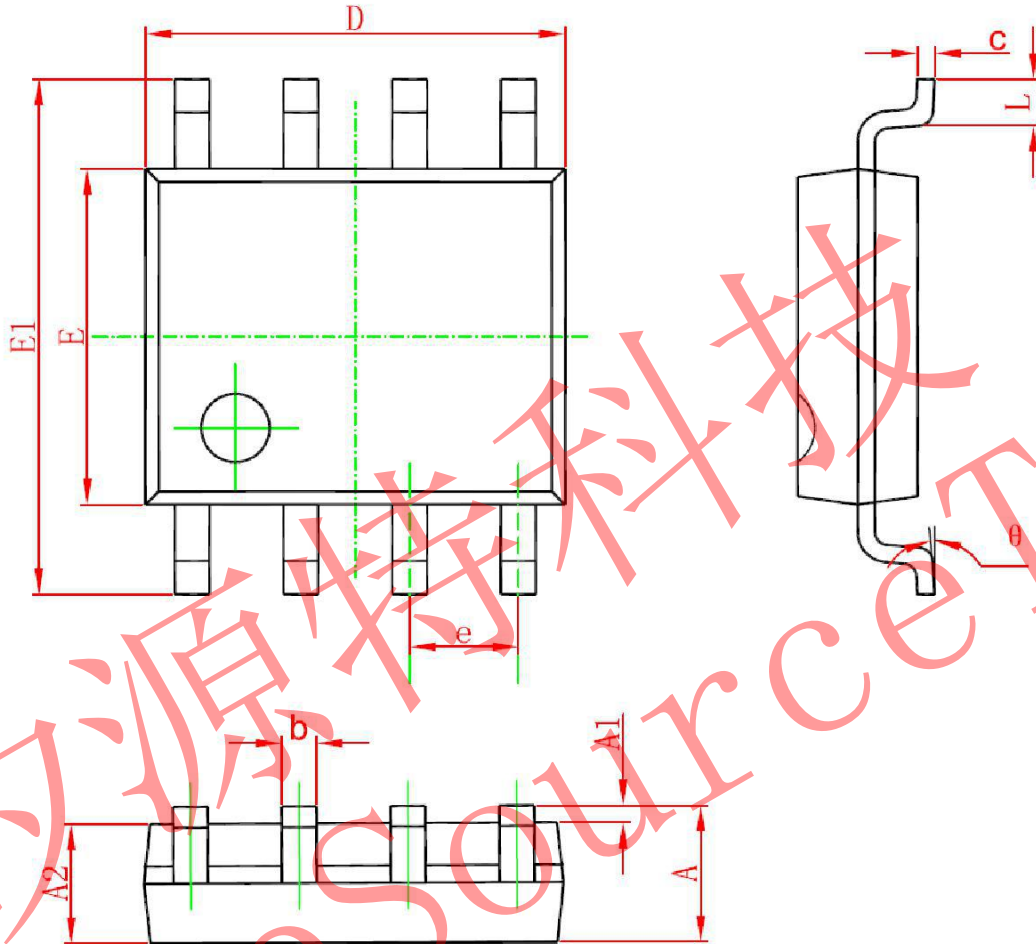


Figure 11 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°